

SECTION I. (AMENDMENT TO THE SPECIFICATION)

1. On page 1, please amend the title of the invention, as follows:

A Semiconductor Structure Having an Abrupt "Delta-Like"

Doping in Si and SiGe films by UHV-CVD Profile

2. On page 1, please add the following section below the title of the invention:

Cross-Reference to Related Application

This is a divisional of U.S. Patent Application No. 08/885,611 filed June 30, 1997 and now U.S. Patent No. 6,723,621.

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